

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L22	3316	MRAM or "magnetic random access memory"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 13:58
L23	166	MTJ adj cells	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 13:59
L24	102	"hard mask" same barrier same spacers	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:52
L25	606	"hard mask" and barrier and spacers	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 14:02
L27	3316	MRAM or "magnetic random access memory"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 13:58
L28	1068	(MTJ adj cells) or "magnetic tunnel junction"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 13:59
L29	678	27 and 28	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 13:59
L30	15	22 and 25	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/21 14:02
L31	51	"hard mask" and barrier and spacers and magnetic	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 14:03
L32	115	"hard mask" and barrier and spacers and (Fe or cobalt or NiFe or CoFe)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 14:04
L33	13	Lee-kye-nam.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 14:05
L34	13	jang-in-woo.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 14:05